OHC850MC

INFRARED EMITTING DIODES

The OHC850MC is a high-power GaAlAs IRED mounted in a TO-18 type header with clear epoxy encapsulation, has wide beam angle and is relatively low-cost compared TO-18 can-type devices.

FEATURES

- High-output power
- High-speed response
- Low profile package

APPLICATIONS

- Optical emitters
- Optical switches
- Transmitting distance with glass cable

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25℃)

Item	Symbol	Cond.	Min.	Typ.	Max.	Unit
Forward voltage	VF	IF=50mA		1.5	1.7	V
Reverse current	IR	VR=5v			10	μA
Radiant intensity	Po	IF=50mA		14		mW/sr
Peak emission wavelength	λp	IF=50mA		850		nm
Spectral bandwidth 50%	Δλ	IF=50mA		30		nm
Half angle	Δθ			±63		deg.

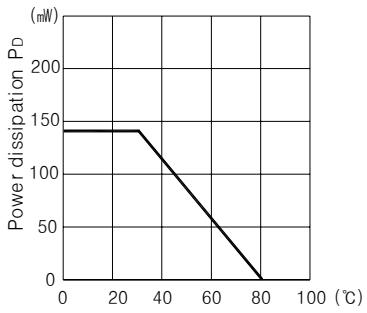
MAXIMUM RATINGS

(Ta=25℃)

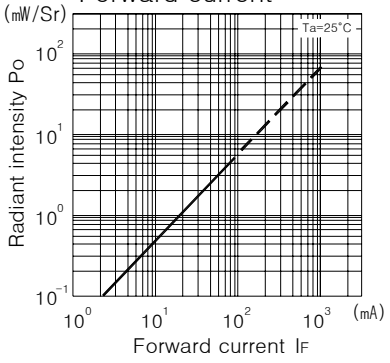
Item	Symbol	Rating	Unit
Reverse voltage	VR	5	V
Forward current	IF	80	mA
Pulse forward current	IFP	1	A
Power dissipation	Pd	140	mW
Operating temp.	Topr	-25～+80	℃
Storage temp.	Tstg	-30～+100	℃
Soldering temp.(1)	Tsol	260	℃

(1)For MAX.5seconds at the position of 2mm from the package

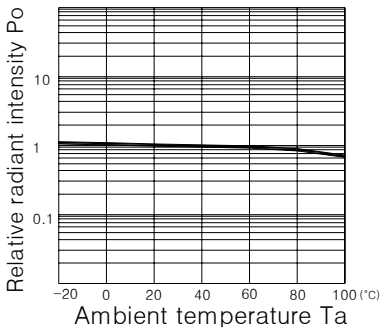
■ Power dissipation Vs Ambient temperature



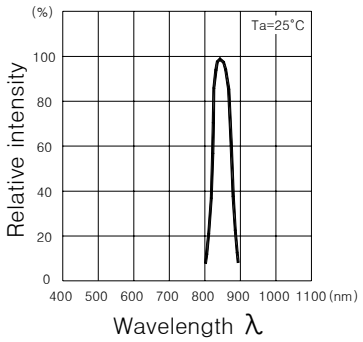
■ Radiant intensity Vs Forward current



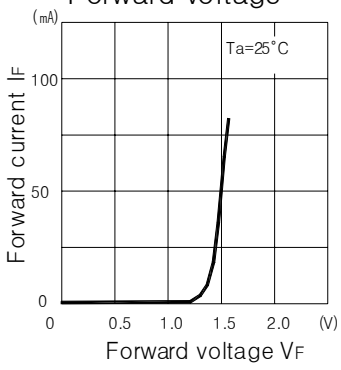
■ Relative radiant intensity Vs Ambient temperature



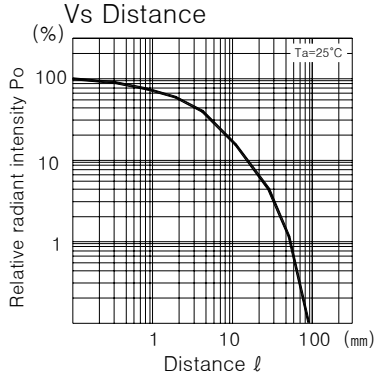
■ Relative intensity Vs Wavelength



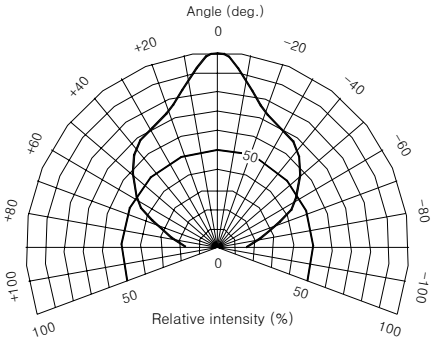
■ Forward current Vs Forward voltage



■ Relative radiant intensity Vs Distance



■ Radiant Pattern



■ DIMENSIONS (Unit:㎜)